

# TO-92 Plastic-Encapsulate Transistors

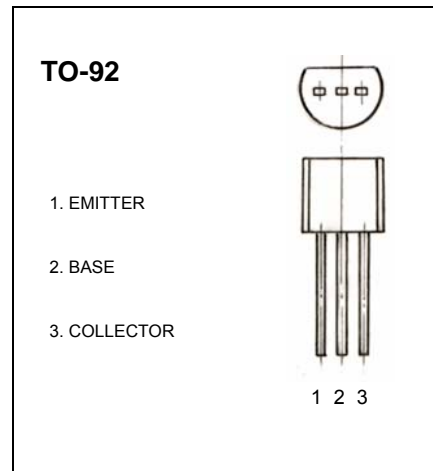
## 2N3904 TRANSISTOR (NPN)

### FEATURE

- NPN silicon epitaxial planar transistor for switching and Amplifier applications
- As complementary type, the PNP transistor 2N3906 is Recommended
- This transistor is also available in the SOT-23 case with the type designation MMBT3904

### MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CB0}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	40	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current -Continuous	0.2	A
$P_C$	Collector Power Dissipation	0.625	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$



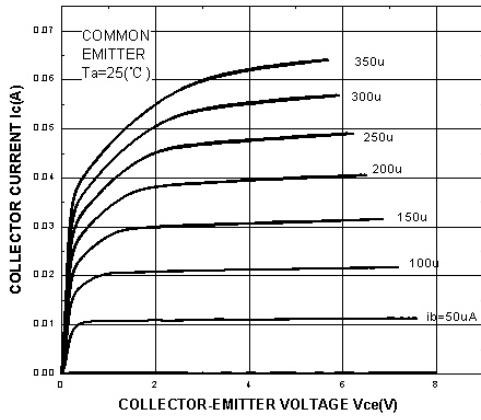
### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}$ , $I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$ , $I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}$ , $I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=60\text{V}$ , $I_E=0$			0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CE}=40\text{V}$ , $I_B=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}$ , $I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE1}$	$V_{CE}=1\text{V}$ , $I_C=10\text{mA}$	100		400	
	$h_{FE2}$	$V_{CE}=1\text{V}$ , $I_C=50\text{mA}$	60			
	$h_{FE3}$	$V_{CE}=1\text{V}$ , $I_C=100\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}$ , $I_B=5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50\text{mA}$ , $I_B=5\text{mA}$			0.95	V
Transition frequency	$f_T$	$V_{CE}=20\text{V}$ , $I_C=10\text{mA}$ , $f=100\text{MHz}$	300			MHz
Delay Time	$t_d$	$V_{CC}=3\text{V}$ , $V_{BE}=0.5\text{V}$ ,			35	ns
Rise Time	$t_r$	$I_C=10\text{mA}$ , $I_{B1}=1\text{mA}$			35	ns
Storage Time	$t_s$	$V_{CC}=3\text{V}$ , $I_C=10\text{mA}$			200	ns
Fall Time	$t_f$	$I_{B1}=I_{B2}=1\text{mA}$			50	ns

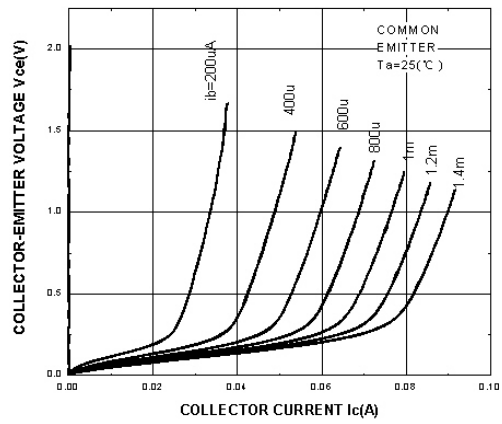
### CLASSIFICATION OF $h_{FE1}$

Rank	O	Y	G
Range	100-200	200-300	300-400

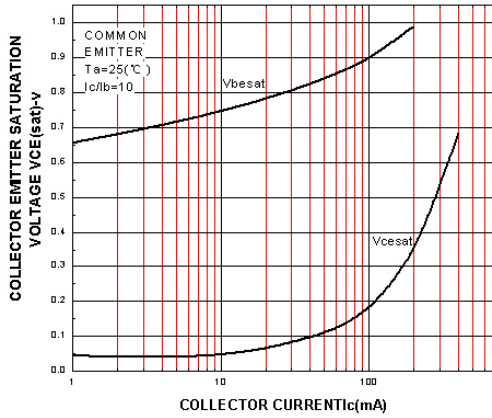
Ic-Vce



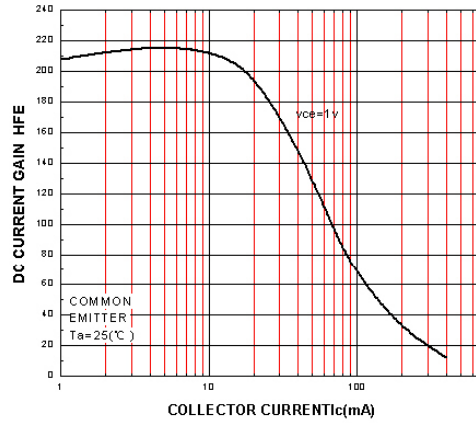
Vce-Ic



Vcesat-Ic  
Vbesat-Ic



hFE-Ic



Pc-Ta

